

Schottky Diode

 $V_{RRM} = 150 V$

 $I_{\text{FAV}} = 6A$

 $V_{\rm F}$ = 0.62 V

High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

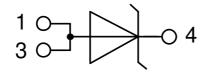
Part number

DSS6-015AS

Marking on Product: 6Y150AS



Backside: cathode



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Data according to IEC 60747and per semiconductor unless otherwise specified

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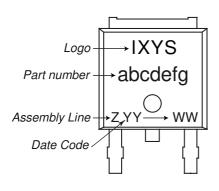
Schottky					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			150	V	
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			150	V	
I _R	reverse current, drain current	$V_R = 150 \text{ V}$	$T_{VJ} = 25^{\circ}C$			250	μΑ	
		$V_R = 150 \text{ V}$	$T_{VJ} = 125$ °C			2.5	mA	
V _F	forward voltage drop	I _F = 6 A	$T_{VJ} = 25^{\circ}C$			0.78	V	
		I _F = 12 A				0.86	٧	
		I _F = 6 A	T _{VJ} = 125°C			0.62	٧	
		I _F = 12 A				0.71	٧	
I _{FAV}	average forward current	T _c = 165°C	T _{vJ} = 175°C			6	Α	
		rectangular $d = 0.5$					 	
V _{F0}	threshold voltage slope resistance $ T_{VJ} = 175^{\circ}C $ for power loss calculation only					0.45	V	
r _F						14.6	mΩ	
R _{thJC}	thermal resistance junction to cas	e				3	K/W	
R _{thCH}	thermal resistance case to heatsi	nk			0.50		K/W	
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			50	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			120	Α	
CJ	junction capacitance	$V_B = 24 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		82		pF	



Package TO-252 (DPak)			Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal 1)			20	Α	
T _{VJ}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				0.3		g	
F _c	mounting force with clip		20		60	N	

¹⁾ l_{nusc} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSS6-015AS-TRL	6Y150AS	Tape & Reel	2500	498912
Alternative	DSS6-015AS-TUB	6Y150AS	Tube	70	525021

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 175 ^{\circ}\text{C}$
$I \rightarrow V_0$)— <u>R</u> o—	Schottky		
V _{0 max}	threshold voltage	0.45		V
$R_{0 \text{ max}}$	slope resistance *	11.4		$m\Omega$

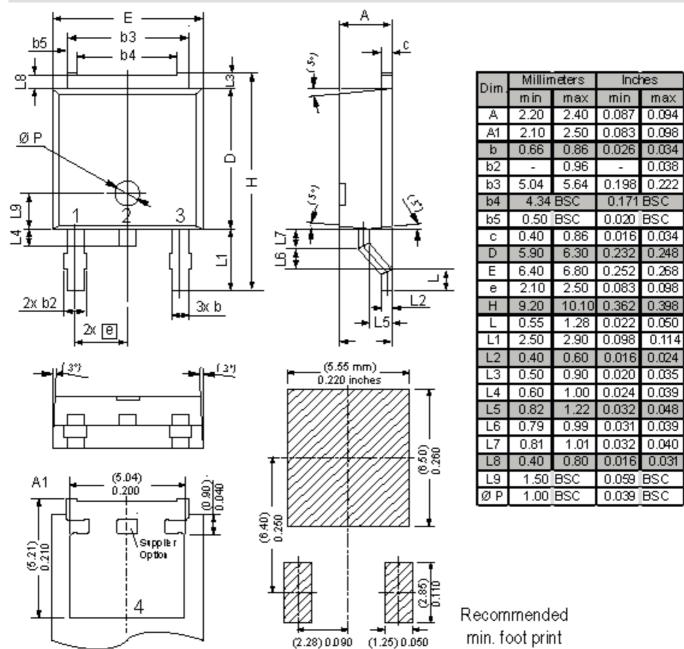
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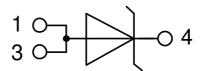
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Outlines TO-252 (DPak)







Schottky

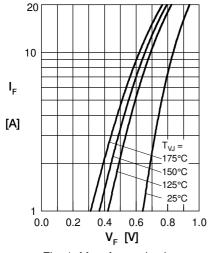


Fig. 1 Max. forward voltage drop characteristics

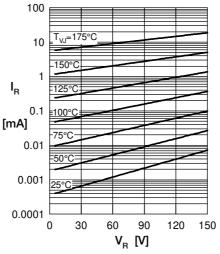


Fig. 2 Typ. reverse current $I_{\rm R}$ vs. reverse voltage $V_{\rm R}$

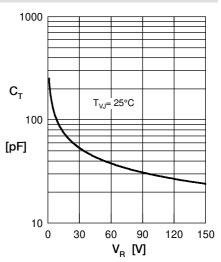


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

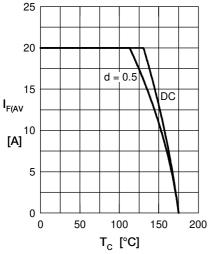


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C

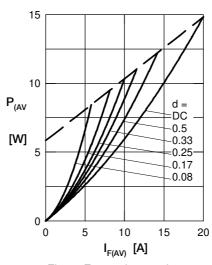


Fig. 5 Forward power loss characteristics

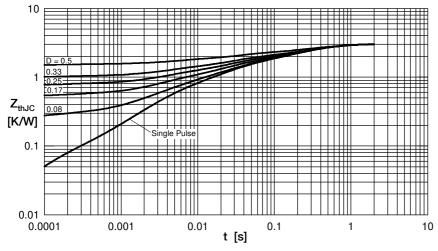


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

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